

ABSTRACT OF THE DISCLOSURE

5 A CVD process for producing nanocrystalline  
films using a plasma (56, 312) created by an argon  
atmosphere (at least about 90 percent by volume)  
10 containing methane (preferably about at least about 1%  
by volume) and optionally hydrogen (preferably 0.001 to  
2% by volume) is described. Strictly controlled gas  
purity and an apparatus which excludes oxygen and  
nitrogen from being introduced from outside of the  
chamber (40, 305) are used. The films are coated on  
various substrates to provide seals, optical  
applications such as on lenses and as a substrate  
material for surface acoustic wave (SAW) devices.

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